



제 32회 한국반도체학술대회

The 32nd Korean Conference on Semiconductors

2025년 2월 12일(수)-14일(금) | 강원도 하이원리조트

Future Normal in Semiconductor

2025년 2월 13일(목), 09:00-10:45

Room G(사파이어 II+III), 5층

J. Nano-Science & Technology 분과

007_[TG1-J] 2D Materials & Devices

좌장: 이철호 교수(서울대학교), 김태욱 교수(전북대학교)

<p>초청 TG1-J-1 09:00-09:30</p>	<p>Hypotaxy of Wafer-Scale Single Crystal Transition Metal Dichalcogenides for Advanced Electronics Gwan-Hyoung Lee Department of Materials Science and Engineering, Seoul National University</p>
<p>TG1-J-2 09:30-09:45</p>	<p>Boltzmann Switching MoS₂ Metal-Semiconductor Field-Effect Transistors Enabled by Monolithic-Oxide-Gapped Metal Gates at the Schottky-Mott Limit Yeon Ho Kim¹, Wei Jiang², Donghoon Moon³, Gwan-Hyoung Lee³, Tony Low², and Chul-Ho Lee³ ¹Korea University, ²University of Minnesota, ³Seoul National University</p>
<p>TG1-J-3 09:45-10:00</p>	<p>Direct Metallization on Cauterized Two-Dimensional Semiconductors for Low-Resistance p-Type Contacts Woo-Ju Lee^{1,2}, Kyu-myung Lee³, GunWoo Yoo^{1,2}, TaeJoon Mo^{1,2}, Yongsup Park^{3,4}, and Cheool-Joo Kim^{1,2} ¹Center for Van der Waals Quantum Solids, IBS, ²Department of Chemical Engineering, POSTECH, ³Department of Physics and Institute of Basic Sciences, Kyung Hee University, ⁴Department of Information Display, Kyung Hee University</p>
<p>TG1-J-4 10:00-10:15</p>	<p>Semimetal Contact Engineering for Low-Noise, High-Performance WSe₂-Based Phototransistors Sunggyu Ryoo¹, Jinwoo Sim¹, Jaeyong Woo¹, Jaehyoung Park¹, Yeeun Kim¹, Youngmin Song¹, Heebeom Ahn², Kyungjune Cho³, and Takhee Lee¹ ¹Department of Physics and Astronomy, Seoul National University, ²Department of Materials Science and Engineering, Seoul National University, ³Convergence Research Center for Solutions to Electromagnetic Interference in Future-Mobility, KIST</p>
<p>TG1-J-5 10:15-10:30</p>	<p>양극성 이황화 몰리브덴 기반 자가구동 광검출기 송준기¹, 황재하¹, 이수연¹, 장한별², 이가영¹ ¹한국과학기술원, ²광주과학기술원</p>



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TG1-J-6	<p data-bbox="427 405 1406 483">Unique Electrical Properties of Junctionless Electric-Double-Layer MoS₂ Transistor with Electrostatically Highly Doped Channel</p> <p data-bbox="427 495 1406 524">Dae Young Jeon¹, Jimin Park², So Jeong Park³, and Gyu Tae Kim⁴</p> <p data-bbox="427 539 1406 568">¹Gyeongsang National University, ²KIST Jeonbuk, ³Korean Intellectual Property Office,</p> <p data-bbox="427 584 612 607">⁴Korea University</p>
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